



Characterization of Stress in GaN-on-Sapphire Microelectromechanical Systems Structures Using Micro-Raman Spectroscopy

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Biblioscholar Nov 2012, 2012. Taschenbuch. Book Condition: Neu. 246x189x6 mm. This item is printed on demand - Print on Demand Neuware - Micro-Raman (Raman) spectroscopy is an e cient, non-destructive techniquewidely used to determine the quality of semiconductor materials and microelectromechanical systems. This work characterizes the stress distribution in wurtzite gal-lium nitride grown on c-plane sapphire substrates by molecular beam epitaxy. Thiswide bandgap semiconductor material is being considered by the Air Force ResearchLaboratory for the fabrication of shockhardened MEMS accelerometers. 100 pp. Englisch.



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